

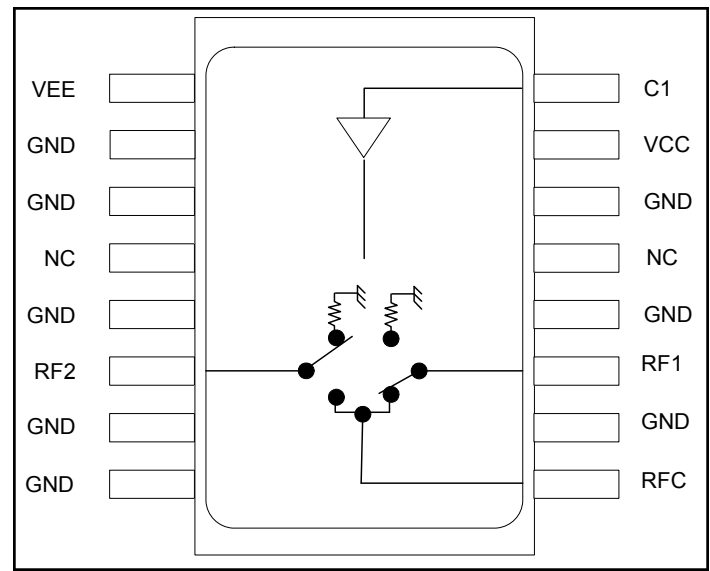
Features

- Typical Isolation: 30 dB (2,000 MHz)
- Typical Insertion Loss: .75 dB (2,000 MHz)
- ASIC TTL/CMOS Driver
- Low DC Power Consumption
- 50 Ohm Nominal Impedance
- Tape and Reel Packaging Available
- Test Boards Available
- SOIC-16 Package

Description

M/A-COM's SW65-0313 is a GaAs MMIC absorptive SP2T switch with an integral silicon ASIC driver. This device is in a 16-lead plastic package. This switch offers excellent broadband performance and repeatability from DC to 3 GHz, while maintaining low DC power dissipation. The SW65-0313 is ideally suited for wireless infrastructure applications. Also available in a ceramic package with improved performance.

Functional Schematic



Pin Configuration¹

Pin No.	Function	Pin No.	Function
1	V _{EE}	9	RFC
2	GND	10	GND
3	GND	11	RF1
4	NC	12	GND
5	GND	13	NC
6	RF2	14	GND
7	GND	15	V _{CC}
8	GND	16	C1

1. NC = No Connection

Ordering Information

Part Number	Package
SW65-0313	Bulk Packaging
SW65-0313TR	1000 piece reel
SW65-0313TB	Sample Test Board

Note: Reference Application Note M513 for reel size information.

**GaAs SP2T Absorptive Switch with
ASIC Driver, DC-3.0 GHz**

Rev. V10

Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50\Omega$

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss	DC - 1.0 GHz	dB	—	0.6	0.75
	DC - 2.0 GHz	dB	—	0.75	0.90
	DC - 3.0 GHz	dB	—	1.2	1.45
Isolation (All arms off)	DC - 1.0 GHz	dB	35	38	—
	DC - 2.0 GHz	dB	27	30	—
	DC - 3.0 GHz	dB	21	24	—
VSWR	DC - 1.0 GHz	—	—	1.2:1	1.3:1
	DC - 2.0 GHz	—	—	1.3:1	1.4:1
	DC - 3.0 GHz	—	—	1.7:1	1.9:1
T_{rise} T_{fall} T_{on} T_{off} Transients	10%/90%, 90%/10% ²	ns	—	15	50
	50% TTL to 90%/10% RF	ns	—	50	150
	In-band (peak to peak)	mV	—	50	150
1 dB Compression	.05 GHz	dBm	—	+25	—
	.5 - 3.0 GHz	dBm	—	+30	—
Input IP ₃	Two tone inputs 0.05 GHz	dBm	—	+40	—
	Up to +5 dBm 0.5 - 3.0 GHz	dBm	—	+46	—
V _{CC}	—	V	+4.5	+5.0	5.5
V _{EE}	—	V	-8.0	-5.0	-4.75
V _{IL} V _{IH}	LOW-level input voltage	V	0.0	—	0.8
	HIGH-level input voltage	V	2.0	—	5.0
I _{in} (Input Leakage Current)	V _{in} = V _{CC} or GND	uA	-1.0	—	1.0
I _{cc} (Quiescent Supply Current)	V _{cntrl} = V _{CC} or GND	uA	—	250	400
ΔI_{cc} (Additional Supply Current Per TTL Input Pin)	V _{CC} = Max, V _{cntrl} = V _{CC} - 2.1 V	mA	—	—	1.0
I _{EE}	V _{EE} min to max, V _{in} = V _{IL} or V _{IH}	mA	-1.0	-0.2	—

2. Decoupling capacitors (.01 μF) are required on the power supply lines.

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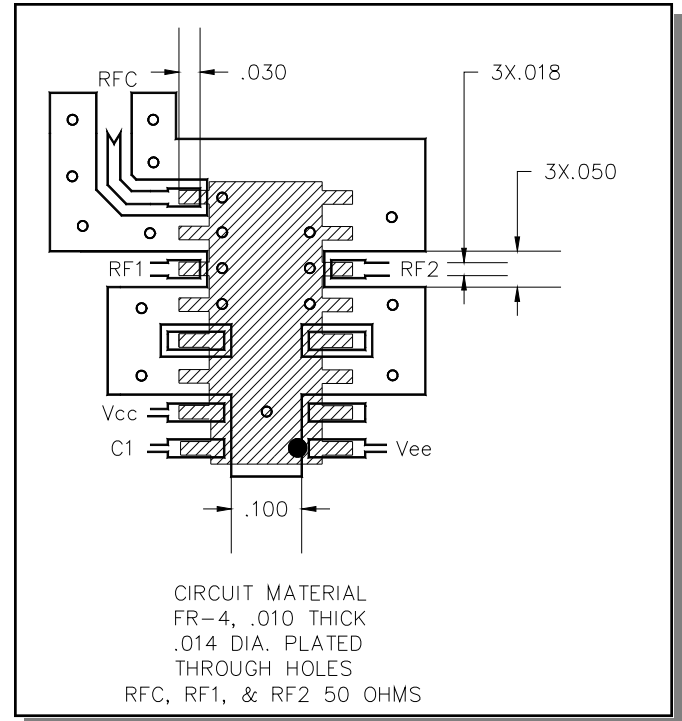
Rev. V10

Absolute Maximum Ratings^{3,4}

Parameter	Absolute Maximum
Max. Input Power 0.05 GHz 0.5 - 3.0 GHz ⁵	+27 dBm +34 dBm
V_{CC}	$-0.5V \leq V_{CC} \leq +7.0V$
V_{EE}	$-8.5V \leq V_{EE} \leq +0.5V$
$V_{CC} - V_{EE}$	$-0.5V \leq V_{CC} - V_{EE} \leq 14.5V$
V_{in} ⁶	$-0.5V \leq V_{in} \leq V_{CC} + 0.5V$
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +125°C

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- When the RF input is applied to the terminated port, the absolute maximum power is +30 dBm.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

Recommended PCB Configuration



Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

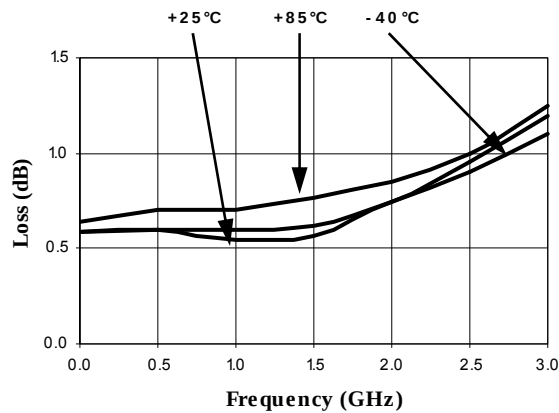
Truth Table (Switch)

C1	RF1	RF2
0	On	Off
1	Off	On

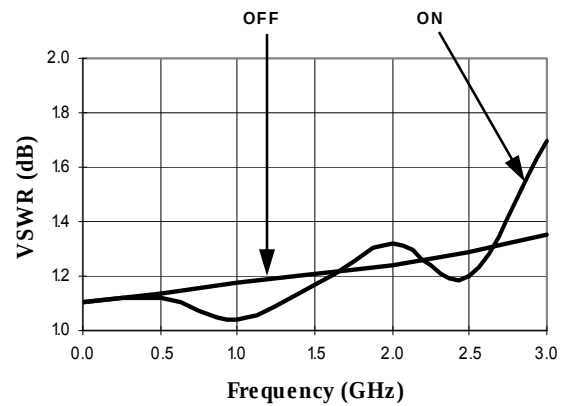
0 = TTL Low; 1 = TTL High

Typical Performance Curves

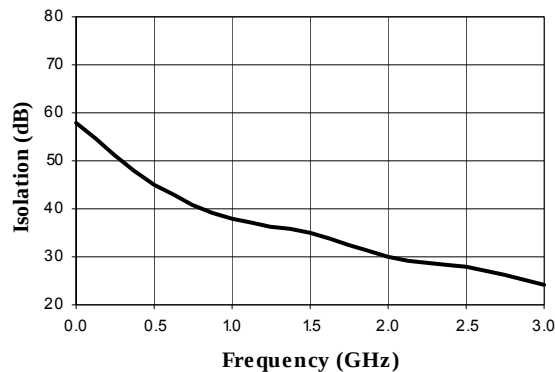
Typical Insertion Loss (dB)



Typical VSWR

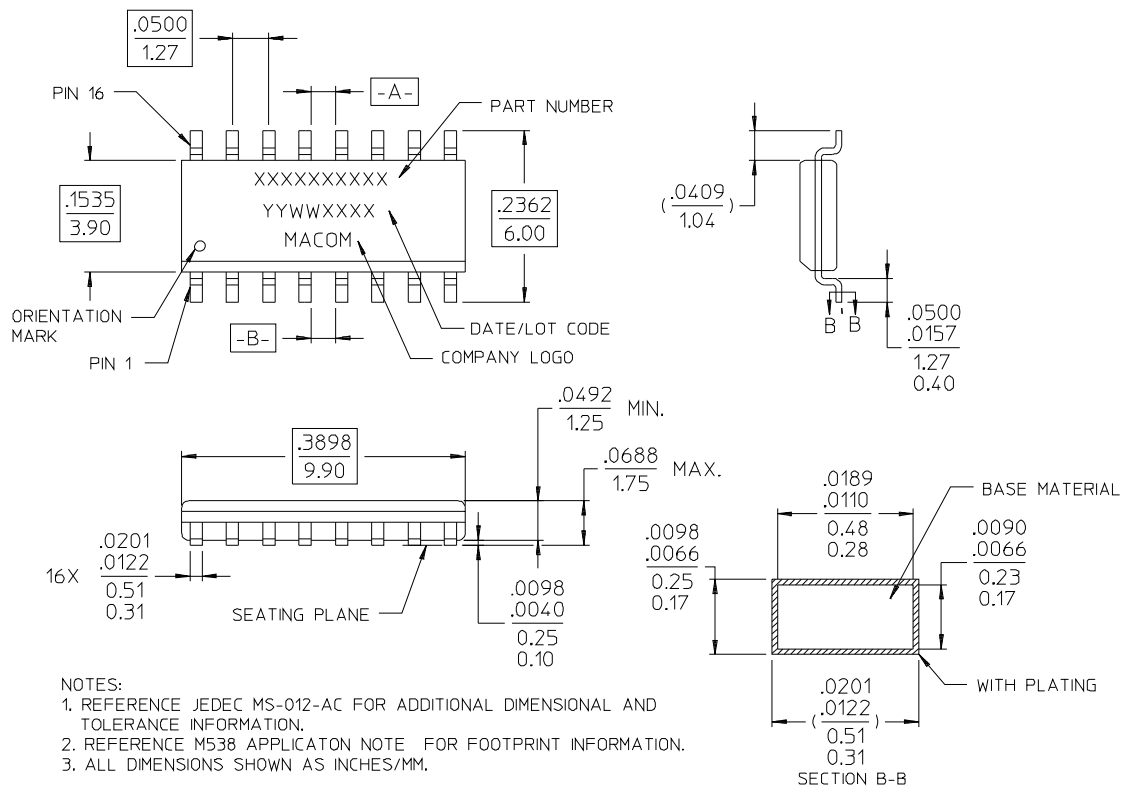


Typical Isolation (dB)



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Rev. V10

SOIC-16[†]

[†] Reference Application Note M538 for lead-free solder reflow recommendations.